

isc Silicon PNP Power Transistor

2SB996

DESCRIPTION

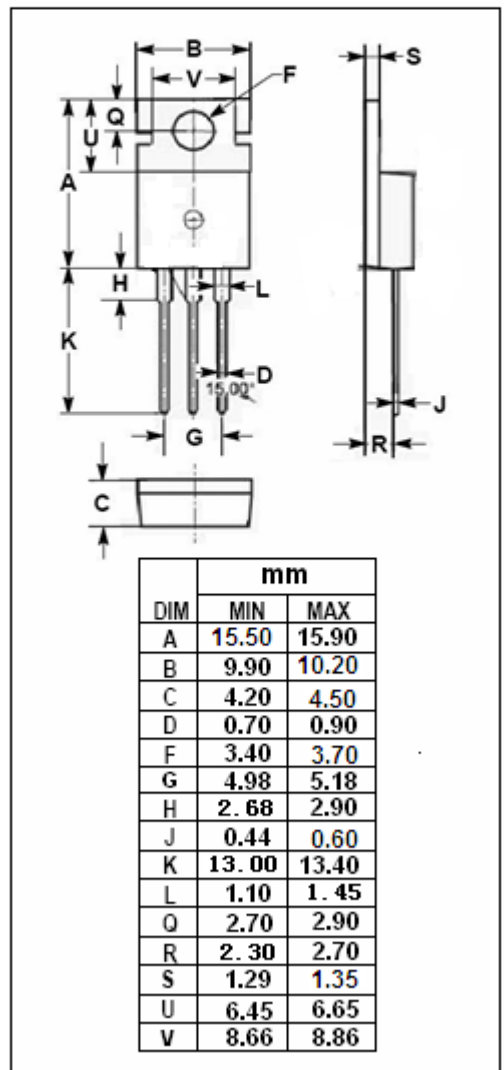
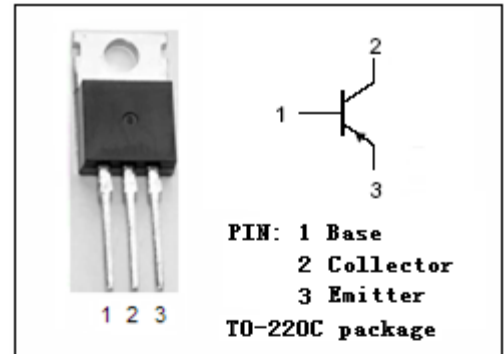
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -80V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SD1356

APPLICATIONS

- Power amplifier applications.
- Recommended for 20~25W high-fidelity audio frequency amplifier output stage.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_B	Base Current-Continuous	-0.4	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB996****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-80			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -0.3A			-1.7	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -3A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-30	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -0.5A; V _{CE} = -5V	40		240	
h _{FE-2}	DC Current Gain	I _C = -3A; V _{CE} = -5V	15			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		130		pF
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -5V		9		MHz

◆ **h_{FE-1} Classifications**

R	O	Y
40-80	70-140	120-240